

IGBT Module Nomenclature

GD **200** **HB** **K** **60** **C2** **S**

GD=IGBT Module

Nominal Current

$I_c(@T_c=80^\circ\text{C})$ as e.g. 200=200A

Circuit Configuration

SG=Single
 CU=Chopper Diode Up Side
 CL=Chopper Diode Low Side
 CE=Common Emitter
 HF=Half Bridge
 HB=Half Bridge + Brake
 HT=Tri-Pack
 HH=H Bridge
 HC=Internal Connected H Bridge
 ML=3 Level, Diode Clamping, NPC1
 MP=Upper Half of NPC1 3 Level
 MN=Lower Half of NPC1 3 Level
 TL=3 Level, IGBT Active Clamping, NPC2
 FF=3 Phase Bridge
 FB=3 Phase Bridge + Brake
 PH=3 Phase Rectifier + 3 Phase Open Emitter Output
 PI=3 Phase Rectifier + Brake + 3 Phase Output
 PJ=3 Phase Rectifier + Brake
 + 3 Phase Open Emitter Output
 PS=Single Phase Rectifier + 3 Phase Output
 PT=Single Phase Rectifier
 + 3 Phase Open Emitter Output
 PU=Single Phase Rectifier + Brake + 3 Phase Output
 PV=Single Phase Rectifier + Brake
 + 3 Phase Open Emitter Output

Die Characteristics

K=Standard IGBT
 U=Ultra Fast IGBT
 L=Low Loss and Fast IGBT
 T=Trench IGBT, Low Loss

Screening Level

P=Unscreened, 25°C Electrical Test (Not for Qualification)

S=Screened for Industrial Applications

H=Screened for High Reliability Applications

Package Type

C1=94mmx34mmx30mm, Cu Base
 C2=106mmx62mmx30mm, Cu Base
 C3=140mmx130mmx38mm, Cu Base
 C4=190mmx140mmx38mm, Cu Base
 C5=107mmx45mmx17mm, Cu Base
 C6=122mmx62mmx17mm, Cu Base
 C7=162mmx150mmx17mm, Cu Base
 C8=94mmx48mmx29mm, Cu Base
 A3=140mmx130mmx38mm, AlSiC Base
 A4=190mmx140mmx38mm, AlSiC Base
 L1=40mmx56mmx20.5mm, DBC Base
 L2=34mmx48mmx15.5mm, DBC Base
 L3=48mmx57mmx15.5mm, DBC Base
 L4=26mmx36mmx15.5mm, DBC Base
 P1=172mmx89mmx38mm, Cu Base
 P2=250mmx89mmx38mm, Cu Base
 P3=113mmx140mmx17mm, Cu Base
 P4=100mmx216mmx17mm, Cu Base
 V1=73mmx140mmx48mm, AlSiC Base
 V2=73mmx140mmx48mm, AlSiC Base

Voltage/10 e.g. 60=600V